



Form 449 (Modified)

**Information Disclosure  
Statement By Applicant**

(Use Several Sheets if Necessary)

Atty Docket No.

UNTYP021

Applicant:

Rinerson et al.

Filing Date

July 30, 2003

Application No.:

10/604,556

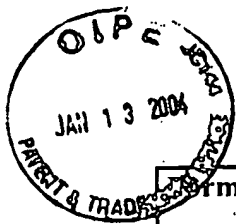
Group

Not Yet Assigned

**Other Documents**

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
TNT	A	Liu, S.Q., et al., "Electric-pulse-induced reversible resistance change effect in magnetoresistive films", Applied Physics Letters, Vol. 76, No. 19, 8 May 2000, 2749-2651.
TNT	B	Liu, S.Q., et al., "A New Concept For Non-Volatile Memory: Electric-Pulse Induced Reversible Resistance Change Effect In Magnetoresistive Films", Space Vacuum Epitaxy Center, University of Huston, Huston TX, 7 Pages.
Examiner	TAN T. NGUYEN	
	Date Considered	10/20/04

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



Form-1449 (Modified)	Atty Docket No. UNTYP021	Application No.: 10/604,556
<b>Information Disclosure Statement By Applicant</b>	Applicant: Rinerson, et al.	Group Not Yet Assigned
(Use Several Sheets if Necessary)	Filing Date July 30, 2003	

#### U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
TNT	A	6,331,944	12/18/01	Monsma, et al.	365	171	4/13/2000
I	B	6,204,139	03/20/01	Liu, et al.	438	385	8/25/1998
TNT	C	5,991,193	11/23/99	Gallagher, et al.	365	171	12/2/1997

#### Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
TNT	O	Beck, A. et al., "Reproducible switching effect in thin oxide films for memory applications," Applied Physics Letters, Vol. 77, No. 1, 3 July 2000, 139-141.
I	P	Rossel, C. et al., "Electrical current distribution across a metal-insulator-metal structure during bistable switching," Journal of Applied Physics, Vol. 90, No. 6, 15 September 2001, 2892-2898.
TNT	Q	Watanabe, Y. et al., "Current-driven insulator-conductor transition and nonvolatile memory in chromium-doped SrTiO <sub>3</sub> single crystals," Applied Physics Letters, Vol. 78, No. 23, 4 June 2001, 3738-3740.
Examiner	TAN T. NGUYEN	
	Date Considered	10/22/04

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.